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Electric field and electron properties of a diffuse nanosecond pulsed discharge in air at atmospheric pressure

<u>A. Brisset^{1,2}</u>, T. Guenin¹, P. Tardiveau¹ and A. Sobota³

¹ Université Paris-Saclay, CNRS, LPGP, 91405 Orsay, France

² Laboratoire EM2C, CNRS, CentraleSupelec, Universite Paris-Saclay, 3, rue Joliot Curie, 91192, Gif-sur-Yvette cedex, France

³ Dept. of Applied Physics, Eindhoven University of Technology, PO Box 513, 5600 MB, Eindhoven, The Netherlands

Context: Atmospheric pressure plasmas (APPs) create large amounts of reactive species. The nature and amount of these species is highly dependent on the space-time electric field distribution (E) of the discharge. E is difficult to tune because it is rapidly screened by the discharge space charge (ps time scale). Because of the E screening, a gas particle is usually only subjected to high fields during the very rapid passage of the E field peak during propagation (~10 - 100ps).

In search for the generation of high energy chemistry, it was suggested some years ago to apply extremely fast and intense voltage rise rates. It was recently demonstrated in [1] that high electric fields (~800 Td) could be maintained shortly with this technique, and this surprisingly induced other remarkable properties of the discharge : i) high stability ii) large volume (cm³ !) iii) high reactivity (~10 times superior to moderate voltage rise rates) *iv*) remains close to ambient temperature (tunable).

Outcomes of this work:

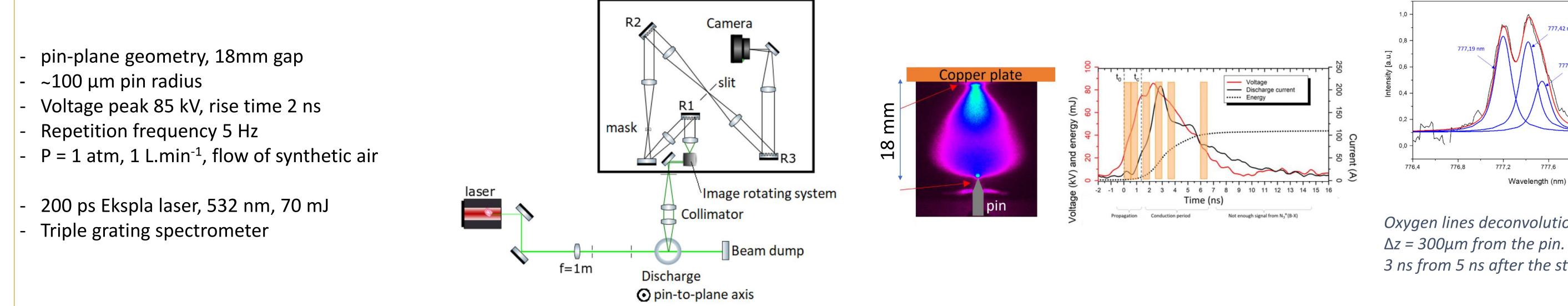
- Specificities of the electron distribution function at high overvoltage: splitting in 2 regions,
- Ground for the control of the filamentation process,
- Ground for the explanation of a ns-electric field rise (~700 Td) in the vicinity of the anode

Methods:

Incoherent Thomson Scattering, **Optical Emission Spectroscopy**, Stark broadening analysis.

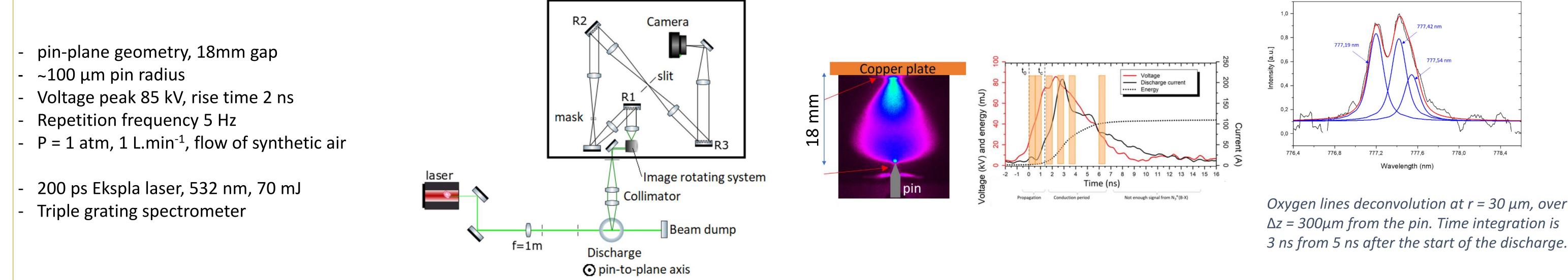
Experimental setup:

Thomson scattering



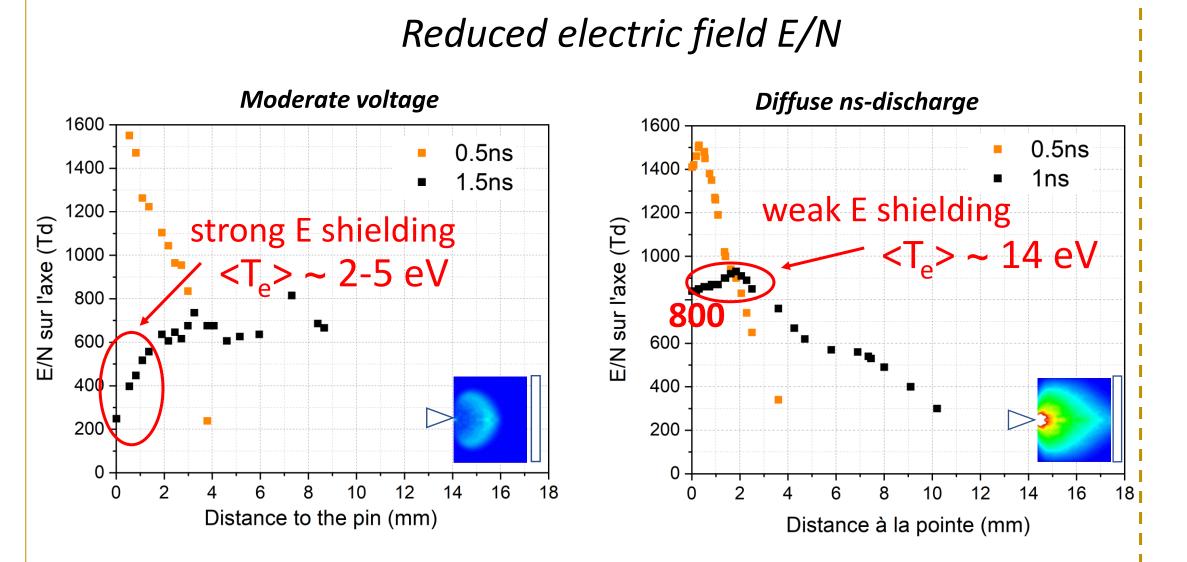
Diffuse Fast Ionization Wave

Stark broadening of O*

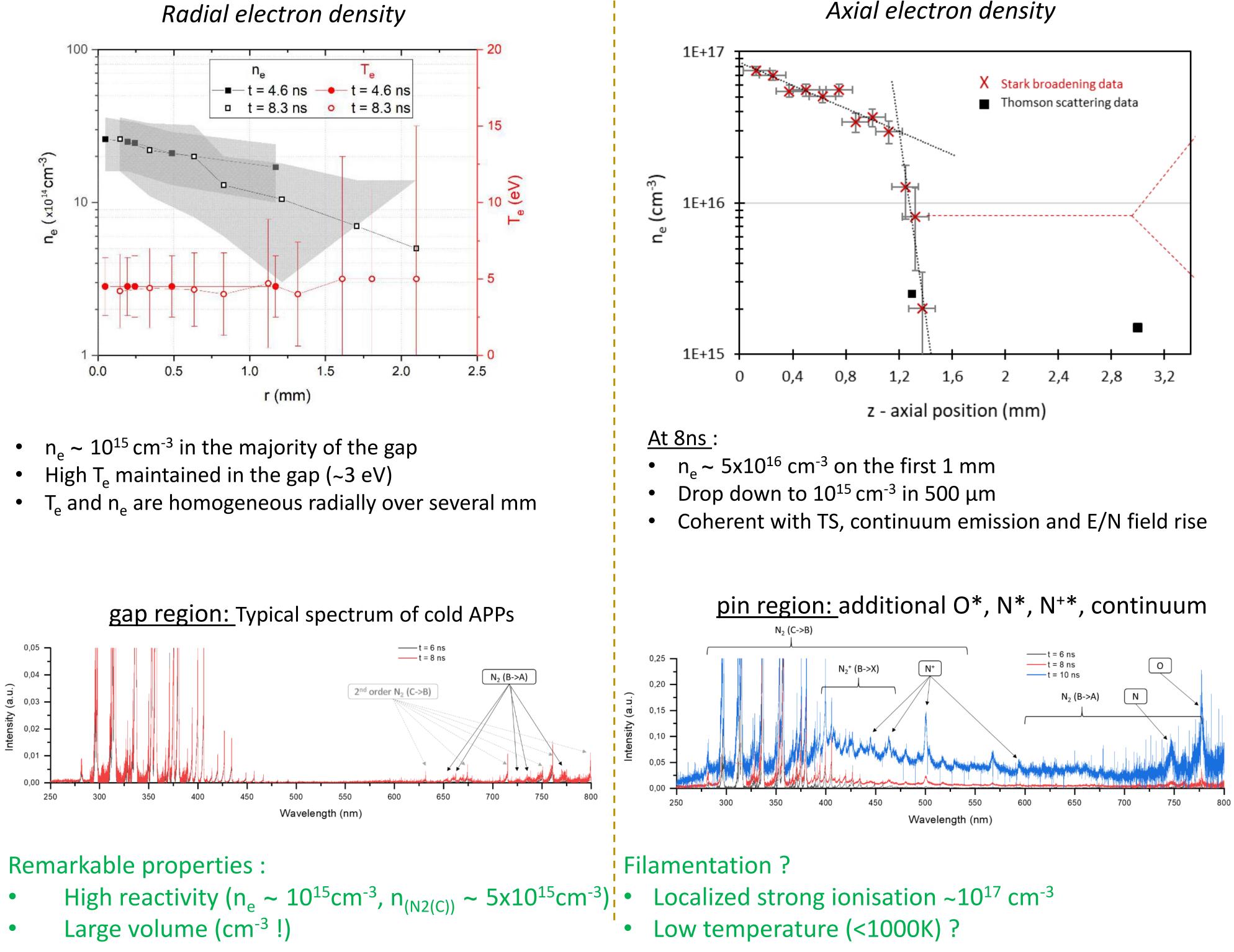


Effect of high overvoltages: maintaining high electric fields, enhancing ionization and dissociation, filamentation?

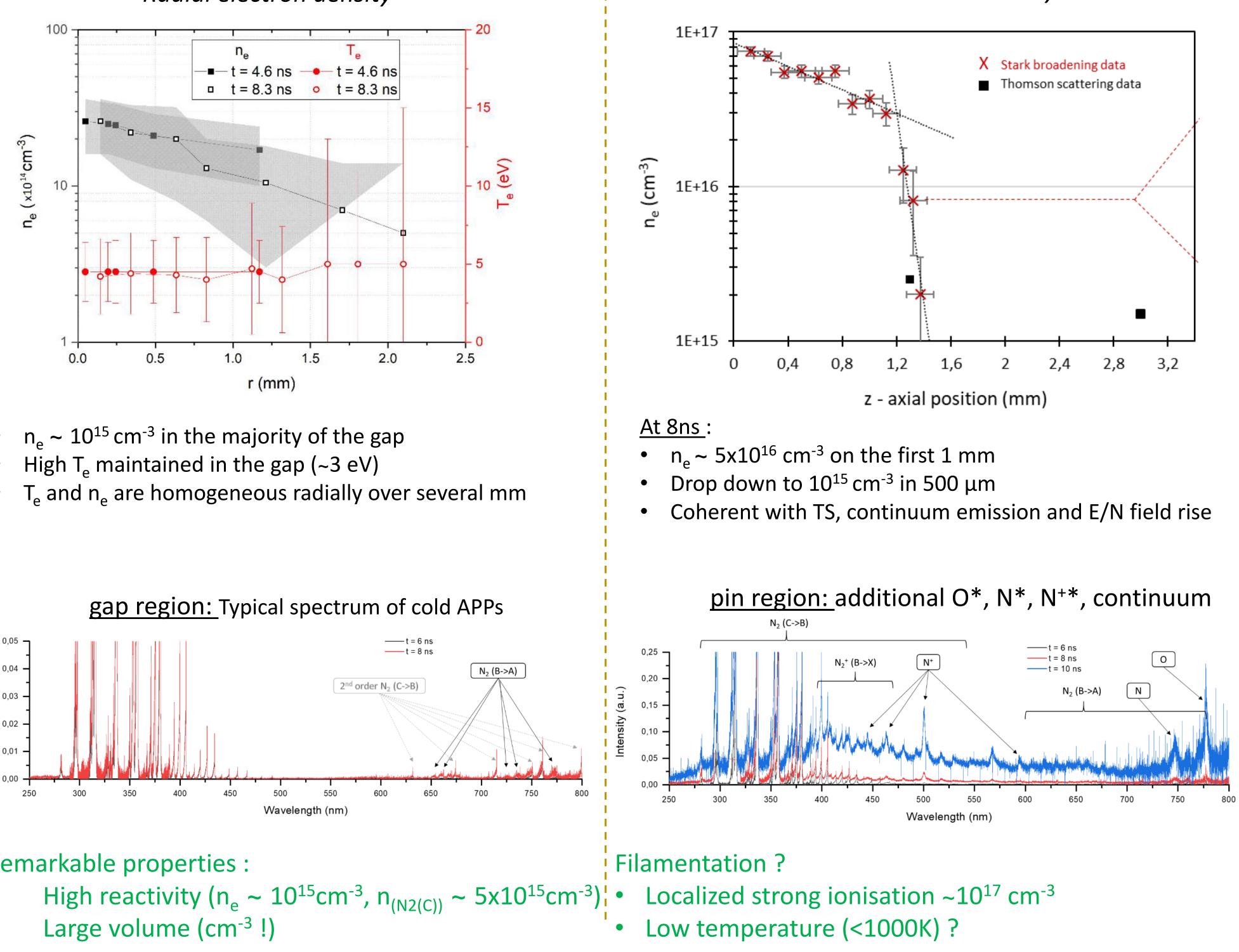
There are fundamental differences in E/N distributions at moderate and at high overvoltage



Region 1 (main gap) is a highly reactive homogeneous glow like discharge

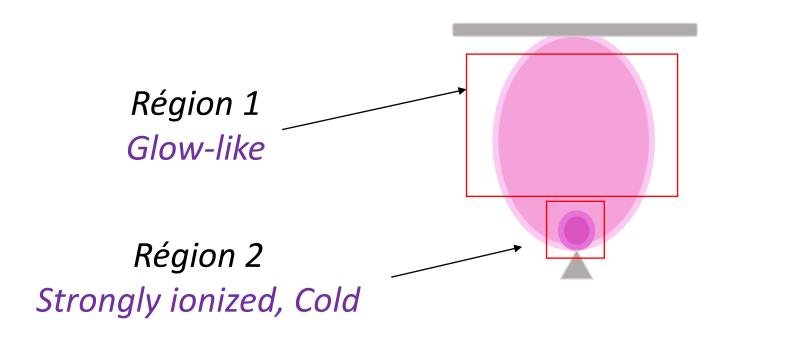


Region 2 (pin vicinity) is a peculiar strongly ionized non-thermal region



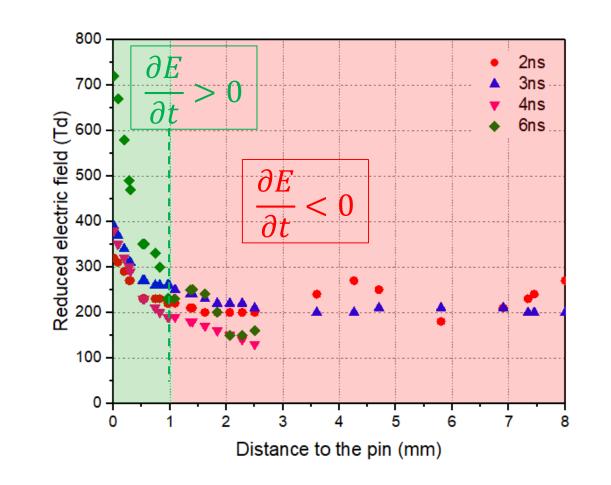
In the diffuse ns-discharge :

- <u>At 500 ps</u>: E/N maximum (~1000 Td) is not located at the discharge emission front.
- <u>At 1 ns</u> : high E/N fields (~800 Td) are maintained from the pin to the position of the field maximum
- <u>At 2-3 ns</u>: E/N homogenizes along the gap (~200 Td)
- <u>At 4-6 ns</u> : E/N rises again strongly (~700 Td) in the vicinity of the pin and decreases in the gap

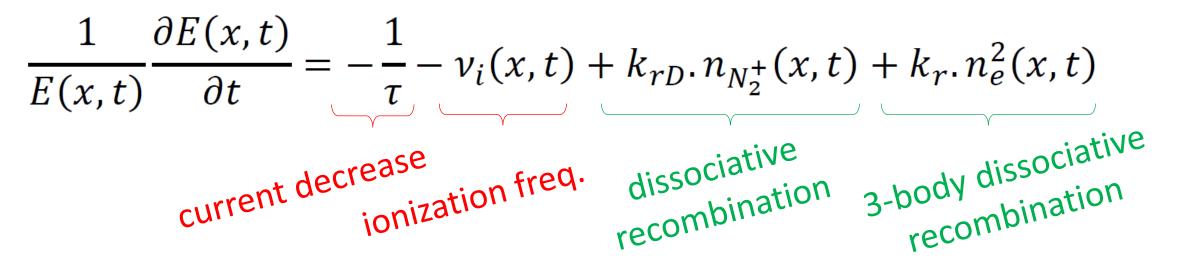


Discharge develops as a highly reactive glow-like discharge and splits after ~ 6 ns in the vicinity of the pin into a high E/N, strongly ionized, region

Kinetics induced ns-electric field rise:



After breakdown and return stroke: $I = e \times n_e \times \mu_e \times E \times S$ Hypothesis, based on high E/N fields in the vicinity of the pin:



In the pin region, E/N is high ($\geq 200 \text{ Td}$):

- Weak attachment processes
- Strong recombination processes
- \Rightarrow Local ns-E field rise ?

Conclusion:

- most of the volume of the discharge (region 1) is quite representative of a quasi-steady state glow discharge
- once propagation is completed (~2 ns) region 1 has rather homogeneous properties ($n_e \sim 10^{15}$ cm⁻³ and $T_e \sim 3$ eV).
- \geq 6 ns, a sub-millimetric region (region 2) develops, characterized by :
 - strong ionization (higher than 1%)
 - $n_{e} \ge 10^{17} \text{ cm}^{-3}$
 - continuum of emission (from UV to near-IR)
 - ns-E field rise

In region 2, the radiative recombination of N_2^+ could help to explain the continuum and a sharp electric field rise (~700 Td)

Perspectives:

- Kinetic model describing ns-E field rise
- Better understanding and control of filamentation

References:

[1] Brisset et al. Plasma Sources Sci. Technol. 28 (2019) 055016

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